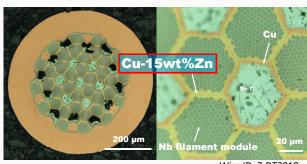


# Fundamental study on the effect of Zn addition into Cu matrix in DT method Nb<sub>3</sub>Sn conductors

Nobuya BANNO (NIMS), Taro MORITA (NIMS, Sophia Univ.), Tsuyoshi YAGAI (Sophia Univ.), Shinya KAWASHIMA (Kobe Steel), Yukinobu MURAKAMI (JASTEC)

#### **Abstract**

Kobe Steel has developed brass matrix DT (distributed tin) method Nb<sub>3</sub>Sn wires, aiming to achieve both high J<sub>c</sub> performance and high robustness, in collaboration with NIMS.



Wire ID: Z-DT2018

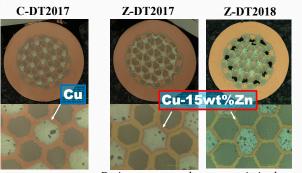
In this work,

Measurerment of Non-Cu  $J_c$  of the developed brass matrix DT wires. Microstructural study on diffusion reaction behavior,

especially during the pre-annealing, towards more detailed optimization of pr

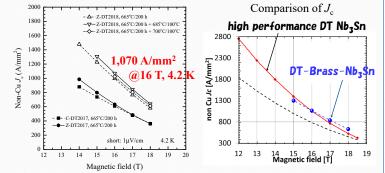
towards more detailed optimization of process parameters and further  $J_{\rm c}$  improvement

	C-DT2017	Z-DT2017	Z-DT2018	High spec DT
Wire diameter (mm)	0.6	0.6	0.6	
Nb ratio within barrier (%)	38.6	38.6	46.6	48.0%
Nb filament diameter (μm)	3.4	3.4	3.4	1.2 µm
Matrix of Nb module	Cu	Cu-15wt%Zn	Cu-15wt%Zr	ı Cu
Matrix of Sn core	Cu	Cu	Cu	
Nb module diameter (μm)	45	45	45	32 µm
Sn diffusion distance (µm)	45	45	45	32 µm
Ti ratio within barrier (wt%)	0.7	0.7	0.6	0.44
Zn ratio within barrier (wt%)	О	5.6	3.9	
Nb / Sn atomic ratio	2.24	2.24	3.0	
Cu / non-Cu ratio	1.12	1.12	1.12	



Design parameters have not optimized yet

## Non-Cu $J_c$ -B characteristics for fabricated wires



Primary heat treatment: 210 °C/6 h + 350 °C/18 h + 460 °C/28 h, + around 570 °C/180 h + 665 °C/200 h

### Microstructural change C-DT2017

#### Completely different



# void Ti compound α-CuSn δ-CuSn δ-CuSn δ-CuSn δ-CuSn δ-CuSn

#### after 400 °C/200 h <sub>+</sub> 480 °C/50 h

 $\beta$ -CuZn phase forms in Z-DT.

Better Sn penetration into Nb module.

Fewer voids form.

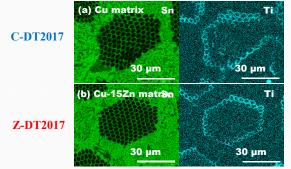


#### after 400 °C/200 h <sub>+</sub> 535 °C/50 h

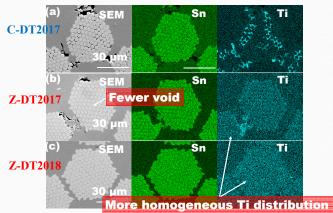
 $\delta$  and  $\beta$  phases started to decompose.

Dendritic mixed phase of  $\delta + \alpha$ 

# Problem of Ti Segregation, when doping Ti to Sn core after 400 C/200 h + 535 C/50 h



#### after Primary heat treatment



#### Conclusion

- Brass DT Nb<sub>3</sub>Sn wires have been developed.
- Zn addition results in  $\beta$ -CuZn formation, suppressing growth of  $\delta + \epsilon$  phases that often cause void growth.
- Zn addition improves Sn and Ti distribution in the Nb filament pack.